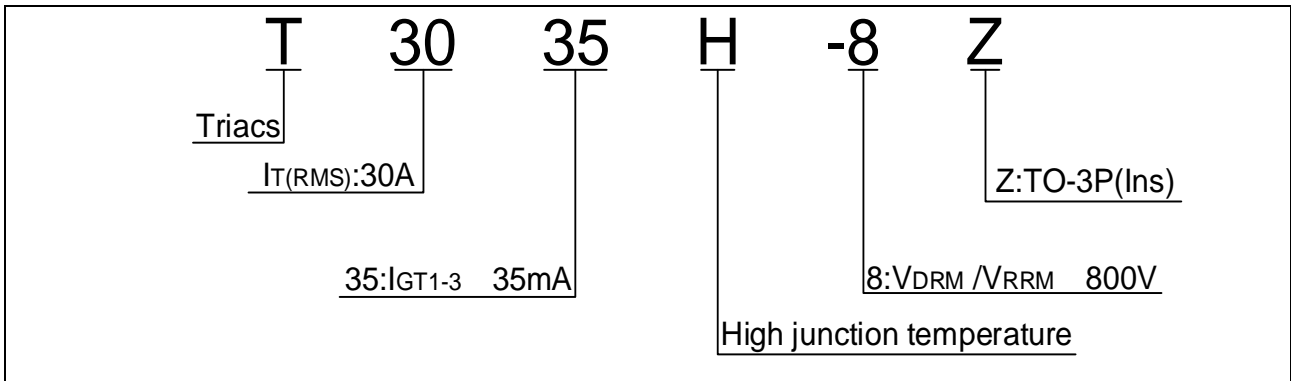


Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbd	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=150$ $R_L=3.3k$	- -	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	70	mA
				80	
I_H	$I_T=500mA$		MAX.	50	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	1000	V/ μs
(dI/dt)c	(dV/dt)c=20V/ μs , $T_j=150$		MIN.	18	A/ms
			TYP.	10	μs
				80	

ORDERING INFORMATION



MARKING

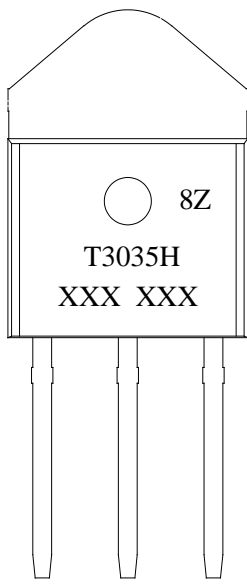


FIG 1: Maxum powpation vMS
on-sate c

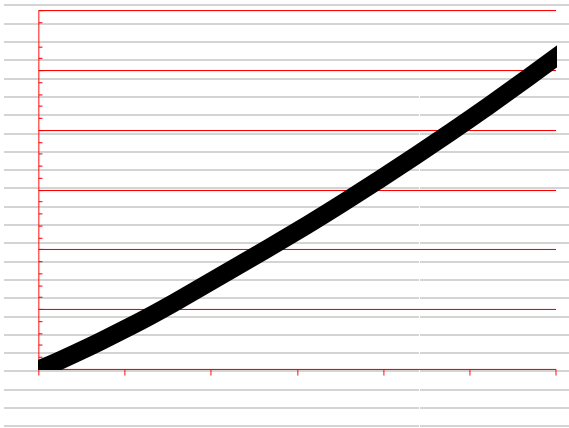


FIG 3: Surge peak on-state current versus
number of cycles



FIG 2: RMS -sate cent v c
temper

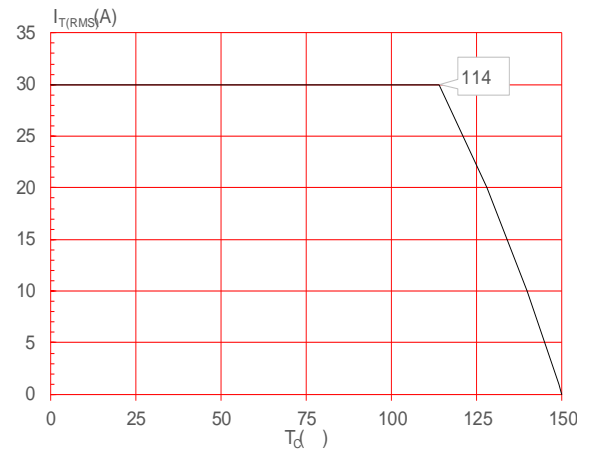
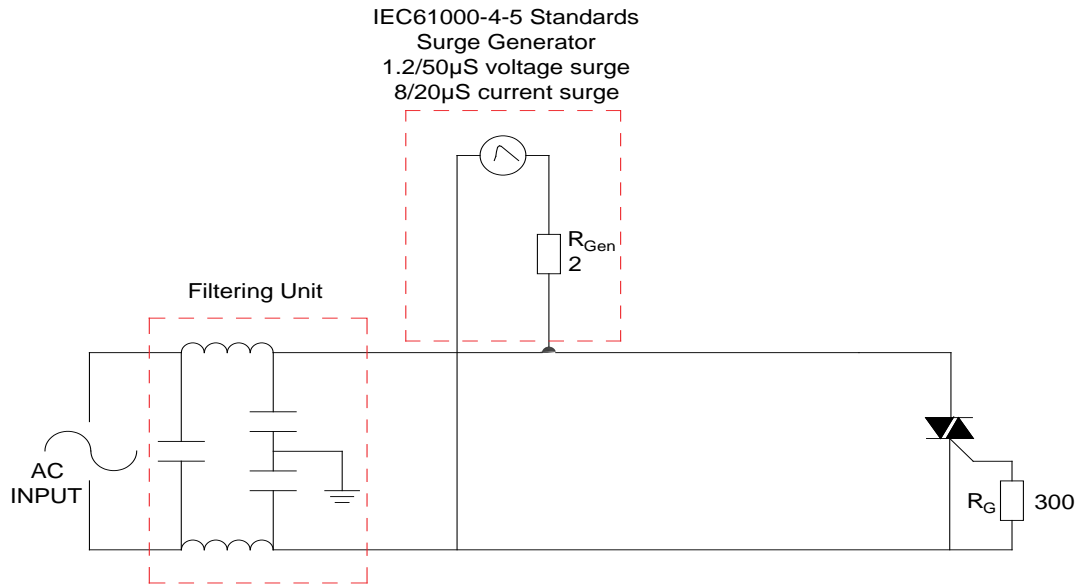


FIG 4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V _{DM} / V _{VM}
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PACKAGE MECHANICAL DATA

